PVD Targets

Honeywell



Honeywell Aluminum Sputtering Targets

Honeywell Aluminum **Sputtering Targets**

PURE ALUMINUM IN MOST STANDARD CONFIGURATIONS



BENEFITS

- Ultrafine, stable grain size
- Patented high strength Aluminum backing plate technology
- Oxide inclusion free
- Low particles
- · Development alloys available

OVERVIEW

Honeywell Electronic Materials' aluminum (AI) targets provide customers outstanding high-volume production capability combined with low operating costs required for today's advanced semiconductor devices.

Honeywell owns and operates one of the world's largest aluminum sputtering target casting operations, ensuring enough aluminum to meet the entire semiconductor market's high volume demand. Our internal casting, forging and manufacturing capabilities yield the most advanced metallurgy, free of defects with consistent performance from target to target.

APPLICATIONS

Al targets deposit a thin, high conformal seed layer of Al onto titanium (Ti) or titanium nitride (TiN) barrier layers.

CONFIGURATIONS

- TEL Anelva AMAT Trikon
- Novellus ULVAC

(Most standard target configurations available)



Omega-P (120µm) 100X







ECAE UFG (8µm) 100X

ECAE SFG (<1µm) 100X

Statically Recrystallized Dynamically Recrystallized

100µm

PERFORMANCE

In-Film Particle Comparison



In-Film Sheet Resistance Comparison



Arc Occurrences Over Target Life



Precipitate

Free

0.5µm



Honeywell Electronic Materials

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TECHNOLOGY COMPARISON ECAE®* Metallurgical Ultrafine Grain Superfine Grain APX **Omega-P** Characteristics (UFG) Condition (SFG) Condition Microstructure Uniform Uniform **Highly Uniform** Highly Uniform Uniformity <5µm uniform <5µm uniform Precipitate Precipitates distribution distribution Free

50µm

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<10µm

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Average Grain Size